Specifcation of products

:

MT400A-Y12

ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

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SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(℃)	VALUE			UNIT
				Min	Type	Max	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, T_C=85°C	125			400	A
$I_{T(RMS)}$	RMS on-state current	Single side cooled, T_C=85°C	125			628	A
V_{DRM} V_{RRM}	Repetitive peakoff-state voltage Repetitive peak reverse voltage	V_{DRM}&V_{RRM} tp=10ms V_{DSM}&V_{RSM}= V_{DRM}&V_{RRM}+200V respectively	125	600		1800	V
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			40	mA
I_{TSM}	Surge on-state current	10ms half sine wave V_R=60%V_{RRM}	125			12.0	KA
I^2t	I^2T for fusing coordination					734	A^2s*10^3
V_{TO}	Threshold voltage		125			0.80	V
r_T	On-state slop resistance					0.49	mΩ
V_{TM}	Peak on-state voltage	I_{TM}=1200A	125			1.5	V
dv/dt	Critical rate of rise of off-state voltage	V_{DM}=67%V_{DRM}	125			800	V/μs
di/dt	Critical rate of rise of, on-state current	From 67%V_{DRM} to 1200A,Gate source 1.5A t_r ≤0.5μs					

OUTLINE DRAWING & CIRCUIT DIAGRAM

MT

Rating and Characteristic

Fig.1

Fig.2

Fig.3

Fig.4

Fig.5

Fig.6

Rating and Characteristic

Fig.7

Fig.8

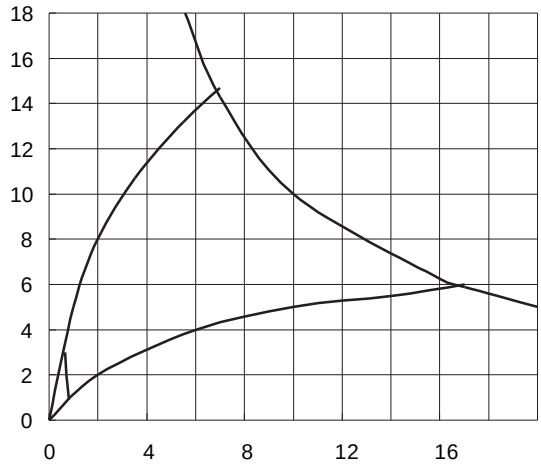

Fig.9

Fig.10

Outside Dimension



